

SEMICONDUCTOR DEVICE HAVING SELF-ALIGNED CONTACT
AND FABRICATING METHOD THEREFOR

SN#09231385

Abstract of the Disclosure

A semiconductor device having a self-aligned contact and a method for fabricating the same are provided. The semiconductor device includes a plurality of conductive patterns formed to be adjacent to one another by sequentially stacking and patterning a first conductive layer and a mask layer on a particular underlying layer. A first insulation layer fills a gap between adjacent conductive layer patterns such that the upper portion of each conductive layer pattern is exposed. A second insulation layer having a spacer shape is formed on the sides of each conductive layer pattern exposed above the first insulation layer. A second conductive layer fills a contact hole which is self-aligned with respect to the second insulation layers between adjacent conductive layer patterns and passes through the first insulation layer.

K:\Samsung\164\164patapp2.wpd